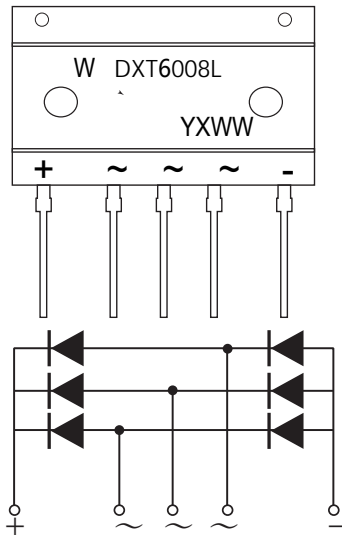


## Low VF Three-phase Bridge Rectifiers



### Features

- Glass Passivated Chip Junction
- Low IRRM
- Low VF
- High VRRM
- Special frame design for heat dissipation

### Benefits

- Case: DXT
- Terminals: Solderable Per MIL-STD-750
- Reduced power loss and switching transistor

Parameter	Symbols	DXT6008L	Units
Maximum Repetitive Peak Reverse Voltage	VRRM	800	V
Maximum RMS voltage	VRMS	560	V
Maximum DC Blocking Voltage	VDC	800	V
Average Rectified Output Current	$I_o$	60	A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	IFSM	450	A
$I^2 t$ rating for fusing ( 1ms < $t$ < 10ms)	$I^2 t$	840	A <sup>2</sup> S
Type Forward Voltage at 30.0A	VF	0.93	V
Maximum Forward Voltage at 30.0 A		1.0	
Maximum DC Reverse Current @TA=25 °C at Rated DC Blocking Voltage @TA=125 °C	IR	10 500	μA
Typical Junction Capacitance (Note1)	Cj	50	pF
Operating and Storage Temperature Range	Tj, Tstg	-55 ~ +150	°C

Note: 1. Measured at 1MHz and applied reverse voltage of 4 VDC.

2. Mounted on glass epoxy PC board with 4×1.5"×1.5" (3.81×3.81 cm) copper pad.

## RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)

Figure 1. Derating Curve Output Rectified Current

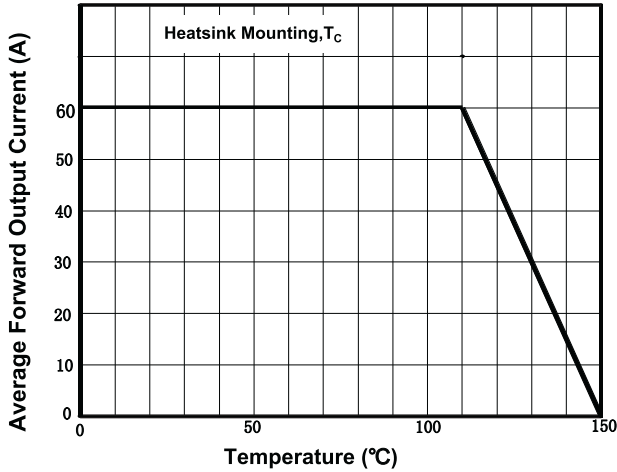


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current per Diode

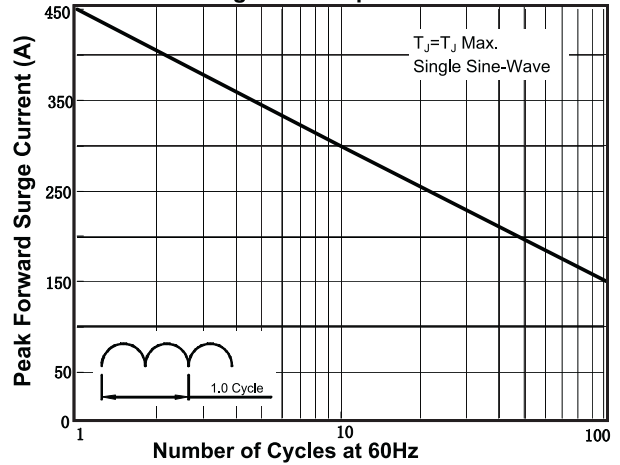


Figure 3. Typical Forward Characteristics Per Diode

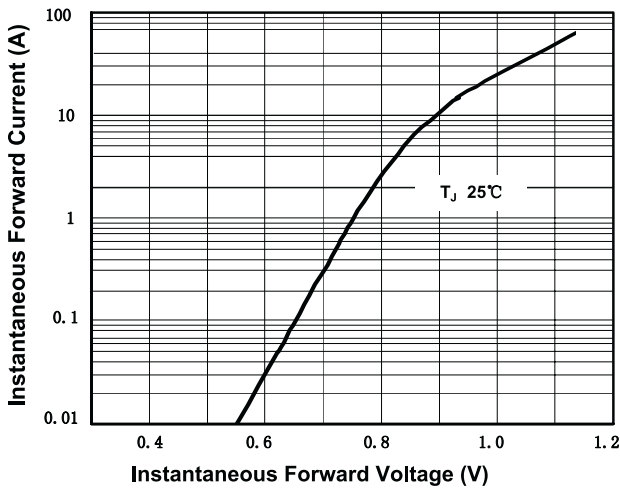


Figure 4. Typical Junction Capacitance Per Diode

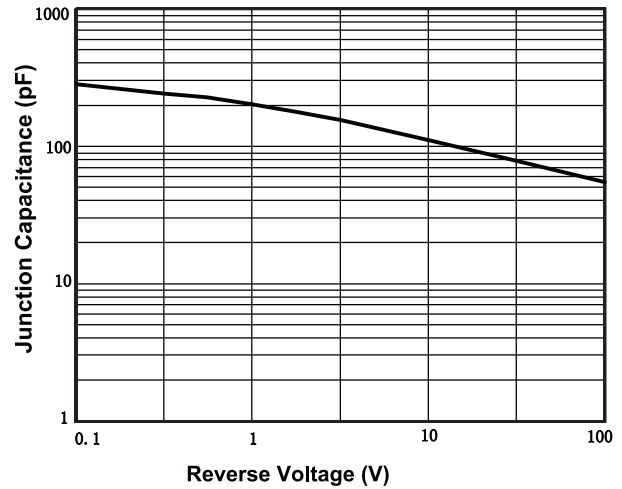
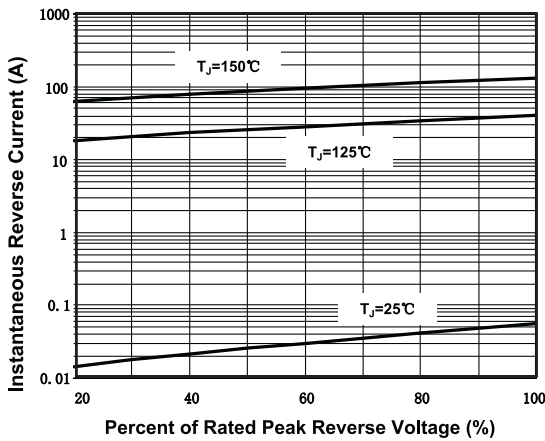


Figure 5. Typical Reverse Characteristics Per Diode



## PACKAGE OUTLINE DIMENSIONS

